ABSTRACT

TREATMENT OF A GERMANIUM LAYER BONDED WITH A SUBSTRATE

The invention relates to a treatment method of a structure comprising a thin Ge layer on a substrate, said layer having been previously bonded with the substrate, the method comprising a treatment to improve the electrical properties of the layer and/or the interface of the Ge layer with the underlying layer, characterised in that said treatment is a heat treatment applied at a temperature between 500°C and 600°C for not more than 3 hours.

The invention also relates to a method to produce a structure comprising a Ge layer, the method comprising bonding between a donor substrate comprising at least in the upper part thereof a thin Ge layer and a receiving substrate, characterised in that it comprises the following steps:

(a) bonding of the donor with the receiving substrate such that the Ge layer is located in proximity to the bonding interface;

(b) removal of the part of the donor substrate not comprising the Ge layer;

(c) treatment of the structure comprising the receiving substrate and the Ge layer in accordance with said treatment method.

Figure 1g

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